TELIC

RECOMMENDED PROCESS FOR TELIC PHOTOMASK BLANKS

PROCESS FOR: Mask Blanks Coated with 1000Å Low Reflective Chrome & 5300Å AZ 1500 Photoresist

Process Step	Chemical	Process Parameter
Exposure	Broadband UV 25 mJ/cm²	
Development	AZ 300 MIF	30 sec.
Rinse	DI Water	40 sec.
Etching	KMG CR-7	60 sec.
Rinse	DI Water	40 sec.
Resist Strip 1	KMG RS-120 100%	15 min. @ 50° C
Resist Strip 2	KMG RS-120 50%	15 min. @ 50° C
Rinse	DI Water	40 sec.
Final Clean	KMG Nanostrip	3 min.
Rinse	DI Water	40 sec.
Spin Dry	N2	60 sec.

RECOMMENDED VENDORS FOR MASK PROCESSING CHEMISTRY

Integrated Micro Materials
www.imicromaterials.com
AZ Electronic Materials
AZ 300 MIF Developer

KMG
www.kmgchemicals.com
CR-7 RS
RS-120
Nano-Strip

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